

A METHOD OF USING FOAMED INSULATORS IN THREE DIMENSIONAL MULTICHIP STRUCTURES

Abstract of the Disclosure

5 A multichip cube structure having a foamed insulating material disposed
between adjacent integrated circuit chips. The foamed insulating material has lower
dielectric constant and therefore reduces the capacitive coupling between electrical
interconnects on adjacent chips. The foamed insulating material also has higher
ductility and lower thermal coefficient of expansion than conventional oxide insulators
10 so as to reduce the occurrence of stress induced cracking in circuitry.

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